

NEC**3 V DUAL DOWNCONVERTER AND
PLL FREQUENCY SYNTHESIZER****UPB1005GS****FEATURES**

- **INTEGRATED RF BLOCK:**
RF & IF Downconverter + PLL frequency synthesizer
- **DOUBLE-CONVERSION:** $f_{1stIF} = 61.380 \text{ MHz}$
 $f_{2ndIF} = 4.092 \text{ MHz}$
- **ADJUSTABLE GAIN:** 20 dB range MIN
- **FIXED DIVISION PRESCALER**
- **LOW POWER CONSUMPTION:** 46.4 mA @ 3 V
- **LOW CURRENT CONSUMPTION:**
 $I_{CC} = 46.4 \text{ mA TYP @ } V_{CC} = 3.0 \text{ V}$
- **SMALL 30 PIN SSOP PACKAGE**
- **TAPE AND REEL PACKAGING AVAILABLE**

DESCRIPTION

The UPB1005GS is a Silicon RFIC designed for low cost GPS receivers. The IC combines a double-conversion RF/IF downconverter block and a PLL frequency synthesizer on one chip. The device operates on a 3 V supply voltage and is housed in a small 30 pin SSOP package, resulting in low power consumption and reduced board space. The device is manufactured using the NESAT™ III 20 GHz fr silicon bipolar process.

NEC's stringent quality assurance and test procedures ensure the highest reliability and performance.

USAGE

- **CONSUMER USE GPS RECEIVER OF REFERENCE FREQUENCY 16.368 MHz, 2ND IF FREQUENCY 4.092 MHz.**

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, $V_{CC} = 3 \text{ V}$, unless otherwise specified)

PART NUMBER PACKAGE OUTLINE			UPB1005GS S30		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
I_{CC}	Total Circuit Current, No Signals	mA		46.4	

RF Downconverter Block ($f_{RFIN} = 1575.42 \text{ MHz}$, $f_{1stLOIN} = 1636.80 \text{ MHz}$, $P_{LOIN} = -10 \text{ dBm}$, $Z_L = Z_S = 50 \Omega$)

I_{CC1}	Circuit Current 1, No Signals	mA		10	
CG_{RF}	RF Conversion Gain, $P_{RFIN} = -40 \text{ dBm}$	dB		15	
NF_{RF}	RF SSB Noise Figure, $P_{RFIN} = -40 \text{ dBm}$	dB		12.5	
$PO_{(sat)RF}$	Maximum IF Output, $P_{RFIN} = -10 \text{ dBm}$	dBm		-5	

IF Downconverter Block ($f_{1stIFIN} = 61.38 \text{ MHz}$, $f_{2ndLOIN} = 65.472 \text{ MHz}$, $Z_S = 50 \Omega$, $Z_L = 2 \text{ k}\Omega$)

I_{CC2}	Circuit Current 2, No Signals	mA		5.3	
CG_{IF}	IF Conversion Gain at Max. Gain, $P_{1stIFIN} = -50 \text{ dBm}$	dB		37	
NF_{IF}	IF SSB Noise Figure at Max. Gain, $P_{1stIFIN} = -50 \text{ dBm}$	dB		15	
$PO_{(sat)IF}$	Maximum 2nd IF Output Level at Max. Gain, $P_{1stIFIN} = -20 \text{ dBm}$	dBm		0	
V_{GC}	Gain Control Voltage, Voltage at Max. Gain of CG_{IF}	V			1.0
GCR	Gain Control Range, $P_{1stIFIN} = -20 \text{ dBm}$	dB	20		

2nd IF Amplifier ($f_{2ndIF} = 4.092 \text{ MHz}$, $Z_S = 50 \Omega$, $Z_L = 2 \text{ k}\Omega$)

I_{CC3}	Circuit Current 3, No Signals	mA		2.4	
$ S_{21} $	Gain $ S_{21} $, $Z_L = 1 \text{ M}\Omega // 27 \text{ pF}^1$	dB		37	
$V_{2ndIFout}$	Output Voltage Swing, $Z_L = 1 \text{ M}\Omega // 27 \text{ pF}^1$	mV _{P-P}	600		

PLL Synthesizer Block

I_{CC4}	Circuit Current 4, PLL, All Blocks Operating	mA		28.7	
f_{PD}	Phase Comparison Frequency, PLL Loop	MHz	8.0	8.184	8.4
V_{REFIN}	Reference Input Minimum Level, $Z_L = 10 \text{ k}\Omega // 20 \text{ pF}^1$	mV _{P-P}	200		
$V_{LP(H)}$	Loop Filter Output Level (H)	V	2.8		
$V_{LP(L)}$	Loop Filter Output Level (L)	V			0.4
V_{REFout}	Reference Output Swing, $Z_L = 1 \text{ M}\Omega // 27 \text{ pF}^1$	V _{P-P}	1.0		

Note:

1. Impedance of measurement equipment.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{CC}	Supply Voltage	V	3.6
I _{CC}	Total Circuit Current	mA	62
P _D	Power Dissipation ²	mW	433
T _{OP}	Operating Temperature	°C	-40 to +85
T _{STG}	Storage Temperature	°C	-55 to +150

Notes:

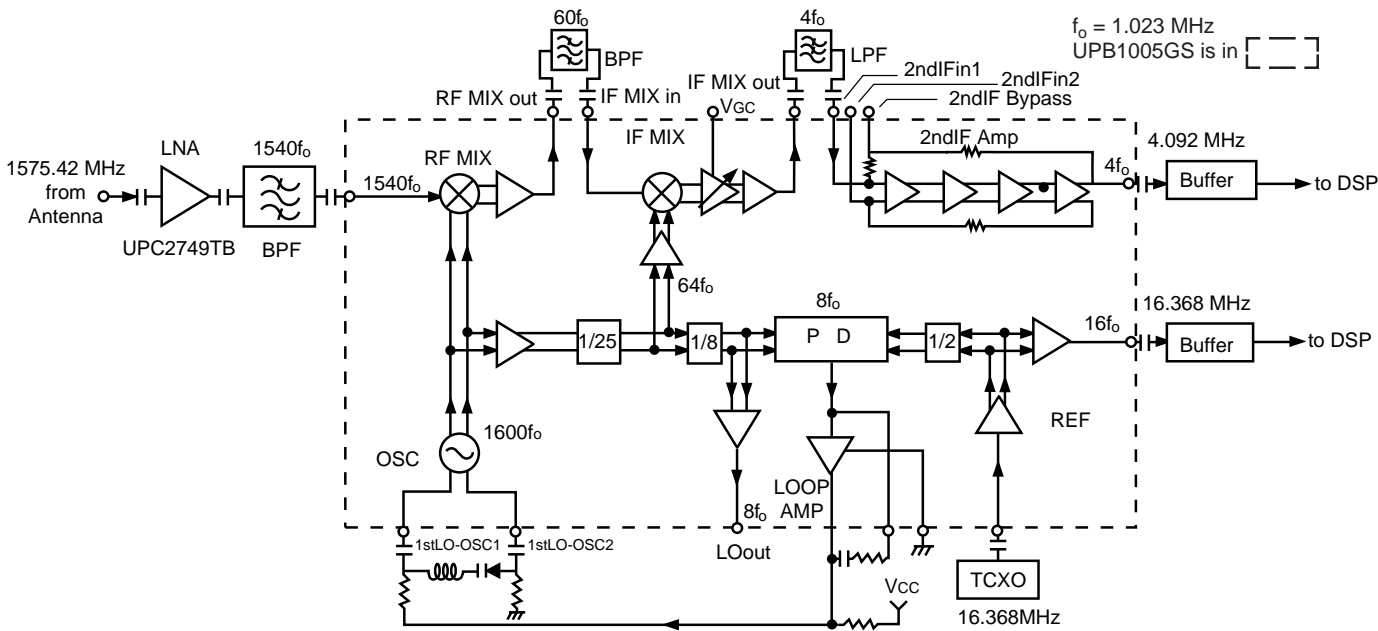
1. Operation in excess of any one of these parameters may result in permanent damage.
2. Mounted on a 50 x 50 x 1.6 mm double-sided copper clad epoxy glass PWB (T_A = +85°C).

RECOMMENDED
OPERATING CONDITIONS

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
V _{CC}	Supply Voltage	V	2.7	3.0	3.3
T _{OP}	Operating Temperature	°C	-40	+25	+85
f _{RFin}	RF Input Frequency	MHz		1575.42	
f _{1stLOin}	1st LO Oscillating Frequency	MHz	1616.8	1636.8	1656.8
f _{1stFIN}	1st IF Input Frequency	MHz		61.38	
f _{2ndLOin}	2nd LO Input Frequency	MHz		65.472	
f _{2ndIFin} f _{2ndIFout}	2nd IF Input/Output Frequency	MHz		4.092	
f _{TCXOin} f _{TCXOout}	Reference Input/Output Frequency	MHz		16.368	

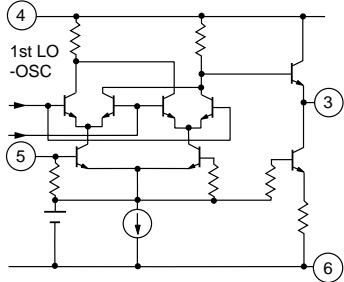
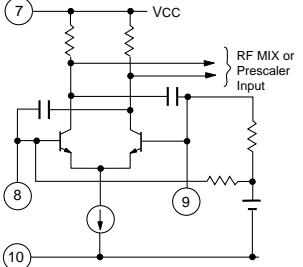
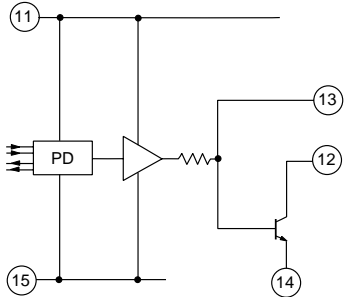
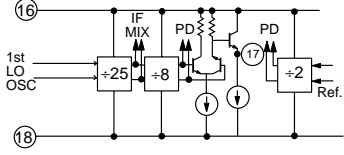
APPLICATION EXAMPLE

GPS Receiver RF Block



Note: This diagram schematically shows only the UPB1005's internal functions on the system. This diagram does not represent the actual application circuit.

PIN FUNCTIONS

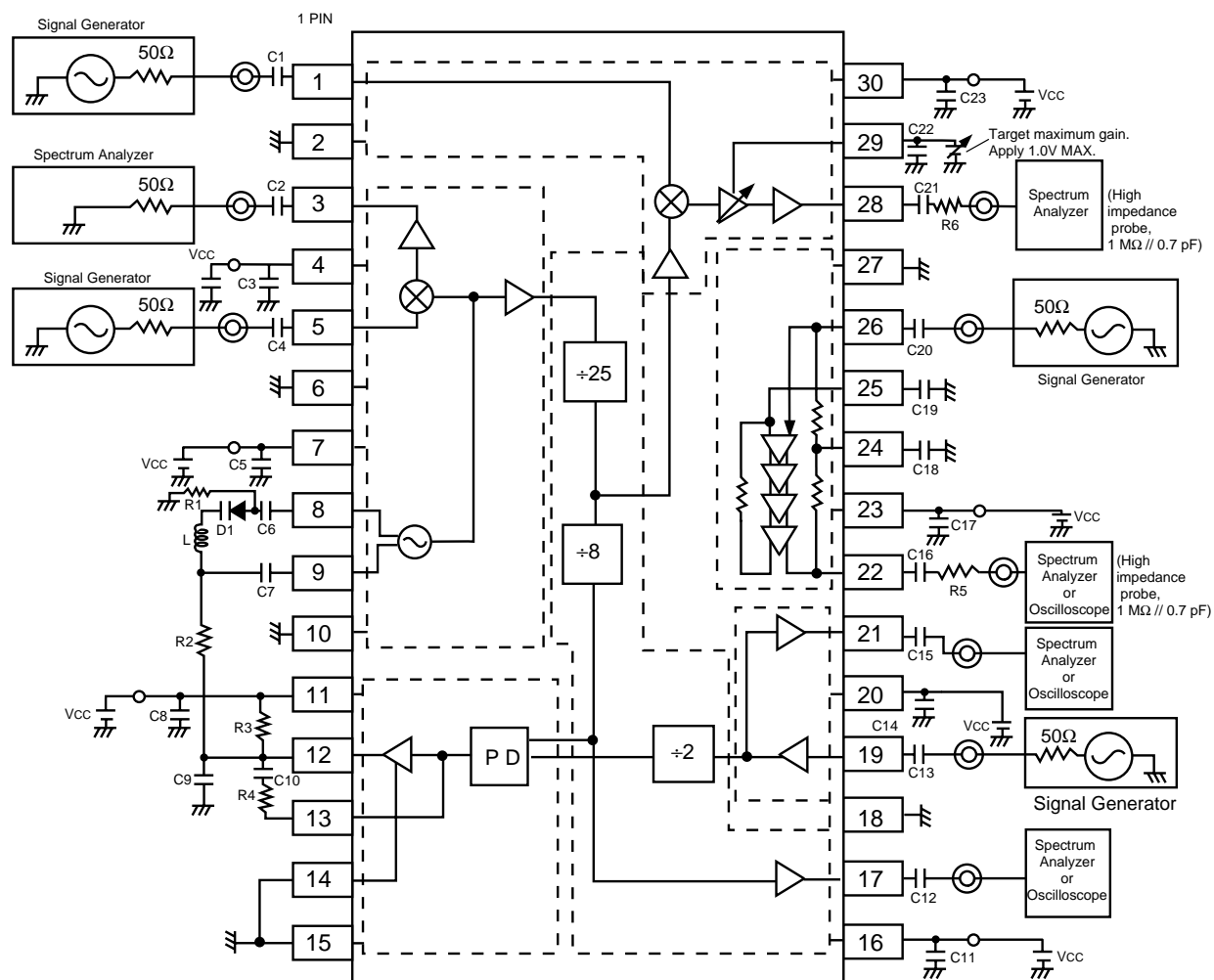
Pin No.	Symbol	Applied Voltage (V)	Pin Voltage (V)	Function and Application	Internal Equivalent Circuit
3	RF MIXout	—	1.68	Output pin of RF mixer. 1st IF filter must be inserted between pin 1 & 3.	
4	Vcc (RF MIX)	2.7 to 3.3	—	Supply voltage pin of RF mixer block. This pin must be decoupled with a capacitor (~1000 pF).	
5	RF MIXin	—	1.20	Input pin of RF mixer. 1 575.42 MHz band pass filter must be inserted between pin 5 and external LNA.	
6	GND (RF MIX)	0	—	Ground pin of RF mixer.	
7	Vcc (1stLO-OSC)	2.7 to 3.3	—	Supply voltage pin of differential amplifier for 1st LO oscillator circuit.	
8	1stLO-OSC1	—	1.75	Pins 8 & 9 are each base pins of the differential amplifier for 1st LO oscillator. These pins should be equipped with LC and varactor circuit to oscillate at 1636.8 MHz as VCO.	
9	1stLO-OSC2	—	1.75		
10	GND (1stLO-OSC)	GND	—	Ground pin of differential amplifier for 1st LO oscillator circuit.	
11	Vcc (phase detector)	2.7 to 3.3	—	Supply voltage pin of phase detector and active loop filter.	
12	PD-Vout3	Pull-up with resistor	—	Pins of active loop filter for tuning voltage output. The active transistors configured with darlington pair are built on-chip. Pin 14 should be connected to ground. Pin 12 to 13 should be equipped with external RC in order to adjust damping factor and cutoff frequency. This tuning voltage output must be connected to varactor diode of 1st LO-OSC.	
13	PD-Vout2	—	Output in accordance with phase difference		
14	PD-Vout1	GND	—		
15	GND (phase detector)	GND	—	Ground pin of phase detector and active loop filter.	
16	Vcc (divider block)	2.7 to 3.3	—	Supply voltage pin of prescalers.	
17	LOout	—	1.98	Monitor pin of comparison frequency at phase detector.	
18	GND (divider block)	GND	—	Ground pin of prescalers and LOout amplifier.	

PIN FUNCTIONS

Pin No.	Symbol	Applied Voltage (V)	Pin Voltage (V)	Function and Application	Internal Equivalent Circuit
19	REFin	—	1.97	Input pin of reference frequency. This pin should be equipped with external TCXO of 16.368 MHz.	
20	Vcc (reference block)	2.7 to 3.3	—	Supply voltage pin of input/output amplifiers in reference block.	
21	REFout	—	1.75	Output pin of reference frequency. The frequency from pin 19 can be measured at 1 V _{p-p} swing.	
22	2ndIFout	—	1.65	Output pin of 2nd IF amplifier. This output is a 4.092 MHz clipped sinewave. This pin should be equipped with external inverter to adjust level to next stage on user's system.	
23	Vcc (2ndIF AMP)	2.7 to 3.3	—	Supply voltage pin of 2nd IF amplifier.	
24	2ndIF bypass	—	2.25	Bypass pin of 2nd IF amplifier input 1. This pin should be grounded through a capacitor.	
25	2ndIFin2	—	2.25	Pin of 2nd IF amplifier input 2. This pin should be grounded through capacitor.	
26	2ndIFin1	—	2.25	Pin of 2nd IF amplifier input 1. 2nd IF filter must be inserted between pins 26 & 28.	
27	GND (2ndIF AMP)	GND	—	Ground pin of 2nd IF amplifier.	
28	IF MIXout	—	1.80	Output pin from IF mixer. IF mixer output signal goes through gain control amplifier before this emitter follower output port.	
29	Vgc (IF MIX)	0 to 3.3	—	Gain control voltage pin of IF mixer output amplifier. This voltage performs forward control (Vgc up → Gain down).	
30	Vcc (IF MIX)	2.7 to 3.3	—	Supply voltage pin of IF mixer, gain control amplifier and emitter follower transistor.	
1	IF MIXin	—	1.18	Input pin of IF mixer.	
2	GND (IF MIX)	0	—	Ground pin of IF mixer.	

Note: Ground pattern on the board must be formed as wide as possible to minimize ground impedance.

TEST CIRCUIT



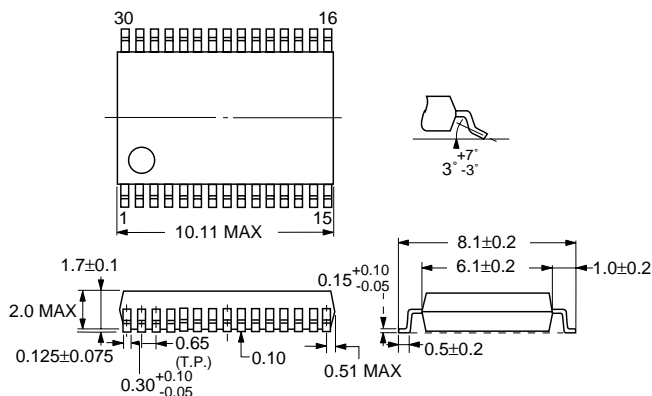
NOTE: Spectrum Analyzer to measure frequency.
Oscilloscope to measure voltage swing.

COMPONENTS LIST

FORM	SYMBOL	VALUE
Chip Capacitor	C1 to C5, C12, C13, C15, C17, C18, C22	1000 pF
	C8, C11, C14, C23	1 μ F
	C6, C7	24 pF (NPO)
	C9	1800 pF
	C19	9900 pF
	C10	33 nF
Ceramic capacitor	C16, C20	0.1 μ F
	C21	0.01 μ F
Chip Resistor	R1, R2	4.7 k Ω
	R3	6.2 k Ω
	R4	1.2 k Ω
	R5, R6	1.95 k Ω
Varactor Diode	D1	HVU12
Chip Inductor	L	2.7 nH

OUTLINE DIMENSIONS (Units in mm)

Package Outline S30

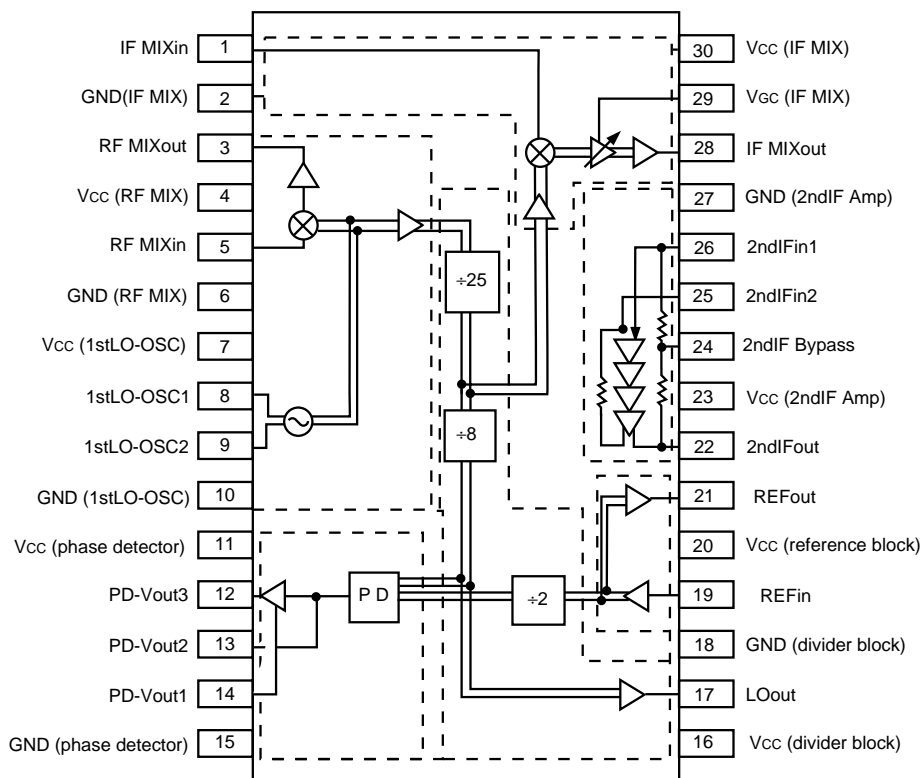


Note:
Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

ORDERING INFORMATION

Part Number	Package	Quantity and Form
UPB1005GS-E1	30 Pin plastic SSOP	Embossed tape 16 mm wide. Qty 2.5 kp/reel. Pin 1 is in tape pull-out direction.

INTERNAL BLOCK DIAGRAM



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